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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

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Group Art Unit: 1732

Application No. 10/017,497

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For: **ULTRAVIOLET LASER ABLATIVE PATTERNING OF  
MICROSTRUCTURES IN SEMICONDUCTORS**

Date:

Examiner: To be assigned

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PRELIMINARY AMENDMENT

TO THE COMMISSIONER FOR PATENTS:

Please amend the above-identified application as follows.

In the Drawings:

FIG. 3 replaces the originally filed FIG. 3.

FIG. 4 replaces the originally filed FIG. 4.

In the Specification:

Please replace the paragraph #0001 on application page 1 with the following paragraph:

-- This patent application derives priority from U.S. Provisional Application No. 60/265,556, filed January 31, 2001, from U.S. Provisional Application No. 60/297,218, filed June 8, 2001, from U.S. Patent Application No. 09/957,633, filed September 19, 2001, which claims priority from U.S. Provisional Application No. 60/233,914, filed September 20, 2000, and from U.S. Patent Application No. 09/803,382, filed March 9, 2001, which claims priority from U.S. Provisional Application No. 60/233,913, filed September 20, 2000. --